

Amendments to the Claims:

The following listing of claims replaces all prior versions, and listings, of claims in the application:

Listing of Claims:

1-2. (canceled)

3. (currently amended) ~~The A semiconductor device as claimed in claim 1~~
having a synthetic high-molecular compound, wherein

the synthetic high-molecular compound covers a semiconductor element
and at least part of electrical connecting means used for electrically connecting
the semiconductor device to external devices;

the synthetic high-molecular compound contains a compound having a
three-dimensional steric structure formed by linking plural third organosilicon
polymers, wherein each of the third organosilicon polymers has a molecular
weight of 2×10^4 to 8×10^5 and is formed by linking a first organosilicon polymer
having a crosslinked structure using siloxane (Si-O-Si combination) with a
second organosilicon polymer having a linear linked structure using siloxane
through siloxane bonds, with covalent bonds resulting from an addition reaction;

the molecular weight of the first organosilicon polymer is lower than that
of the second organosilicon polymer;

the semiconductor element is selected from the group consisting of a SiC
semiconductor element using a wide gap semiconductor and a GaN
semiconductor element using a wide gap semiconductor,

the first organosilicon polymer is selected from the group consisting of
polyphenylsilsesquioxane, polymethylsilsesquioxane, polyethylsilsesquioxane,
polypropylsilsesquioxane, and combinations thereof; and

the second organosilicon polymer is selected from the group consisting of
polydimethylsiloxane, polydiethylsiloxane, polydiphenylsiloxane,
polymethylphenylsiloxane, and combinations thereof.

4. (currently amended) ~~The A~~ semiconductor device ~~as claimed in claim 1~~
having a synthetic high-molecular compound, wherein

the synthetic high-molecular compound covers a semiconductor element
and at least part of electrical connecting means used for electrically connecting
the semiconductor device to external devices;

the synthetic high-molecular compound contains a compound having a
three-dimensional steric structure formed by linking plural third organosilicon
polymers, wherein each of the third organosilicon polymers has a molecular
weight of 2×10^4 to 8×10^5 and is formed by linking a first organosilicon polymer
having a crosslinked structure using siloxane (Si-O-Si combination) with a
second organosilicon polymer having a linear linked structure using siloxane
through siloxane bonds, with covalent bonds resulting from an addition reaction;

the molecular weight of the first organosilicon polymer is lower than that
of the second organosilicon polymer;

the semiconductor element is selected from the group consisting of a wide
gap semiconductor light-receiving element, a wide gap semiconductor light-
emitting element, and a combination thereof,

the first organosilicon polymer is selected from the group consisting of
polyphenylsilsesquioxane, polymethylsilsesquioxane, polyethylsilsesquioxane,
polypropylsilsesquioxane, and combinations thereof; and

the second organosilicon polymer is selected from the group consisting of
polydimethylsiloxane, polydiethylsiloxane, polydiphenylsiloxane,
polymethylphenylsiloxane, and combinations thereof.

5-15. (canceled)